

## 1. General description

Silicon Carbide Schottky diode in a DFN 8\*8 plastic package, designed for high frequency switched-mode power supplies.

## 2. Features and benefits

- Highly stable switching performance
- High forward surge capability IFSM
- Extremely fast reverse recovery time
- Superior in efficiency to Silicon Diode alternatives
- Reduced losses in associated MOSFET
- Reduced EMI
- Reduced cooling requirements
- RoHS compliant

## 3. Applications

- Power factor correction
- Telecom / Server SMPS
- UPS
- PV inverter
- PC Silverbox
- LED / OLED TV
- Motor Drives

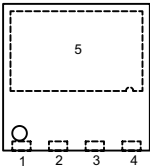
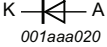
## 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Values			Unit
<b>Absolute maximum rating</b>						
$V_{RRM}$	repetitive peak reverse voltage		650			V
$I_{F(AV)}$	average forward current	$\delta = 0.5$ ; square-wave pulse; $T_c \leq 153$ °C; <a href="#">Fig. 1</a> ; <a href="#">Fig. 2</a> ; <a href="#">Fig. 3</a>	6			A
$T_j$	junction temperature		175			°C
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
$V_F$	forward voltage	$I_F = 6$ A; $T_j = 25$ °C; <a href="#">Fig. 5</a>	-	1.5	1.7	V
		$I_F = 6$ A; $T_j = 150$ °C; <a href="#">Fig. 5</a>	-	1.8	2.1	V
<b>Dynamic characteristics</b>						
$Q_r$	recovered charge	$I_F = 6$ A; $dI_F/dt = 500$ A/ $\mu$ s; $V_R = 400$ V; $T_j = 25$ °C; <a href="#">Fig. 7</a>	-	9	-	nC

## 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	n.c.	not connected		
2	n.c.	not connected		
3	A	anode		
4	A	anode		
5	K	mounting base; connected to cathode		

## 6. Ordering information

Table 3. Ordering information

Type number	Package name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
GKTSC06650T	DFN8*8	GKTSC06650T6J	Tape	3000	DFN8X8N	25-Dec-2015

## 7. Marking

Table 4. Marking codes

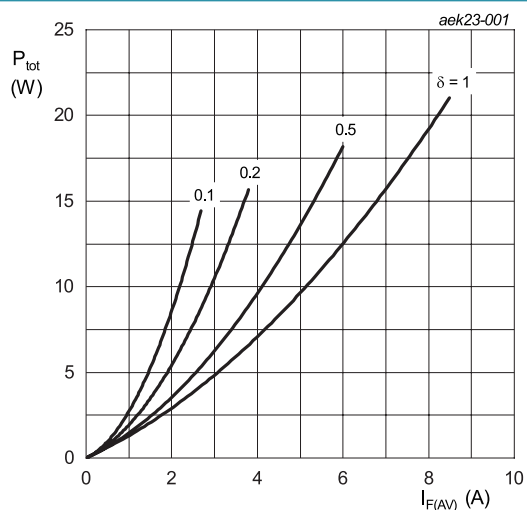
Type number	Marking codes
GKTSC06650T	GKTSC 06650T

## 8. Limiting values

**Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

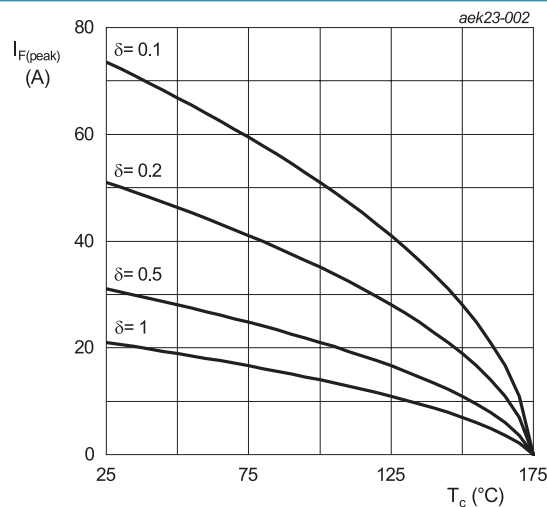
Symbol	Parameter	Conditions	Values	Unit
$V_{RRM}$	repetitive peak reverse voltage		650	V
$V_{RWM}$	crest working reverse voltage		650	V
$V_R$	reverse voltage	DC	650	V
$I_{F(AV)}$	average forward current	$\delta = 0.5$ ; square-wave pulse; $T_c \leq 153\text{ }^\circ\text{C}$ ; <a href="#">Fig. 1</a> ; <a href="#">Fig. 2</a> ; <a href="#">Fig. 3</a>	6	A
$I_{FRM}$	repetitive peak forward current	$\delta = 0.5$ ; $t_p = 25\text{ }\mu\text{s}$ ; $T_c \leq 153\text{ }^\circ\text{C}$ ; square-wave pulse	12	A
$I_{FSM}$	non-repetitive peak forward current	$t_p = 10\text{ ms}$ ; $T_{j(\text{init})} = 25\text{ }^\circ\text{C}$ ; sine-wave pulse	36	A
		$t_p = 10\text{ }\mu\text{s}$ ; $T_{j(\text{init})} = 25\text{ }^\circ\text{C}$ ; square-wave pulse	310	A
$I^2t$	$I^2t$ for fusing	sine-wave pulse; $T_{j(\text{init})} = 25\text{ }^\circ\text{C}$ ; $t_p = 10\text{ ms}$	6	$\text{A}^2\text{s}$
$T_{stg}$	storage temperature		-55 to 175	$^\circ\text{C}$
$T_j$	junction temperature		175	$^\circ\text{C}$



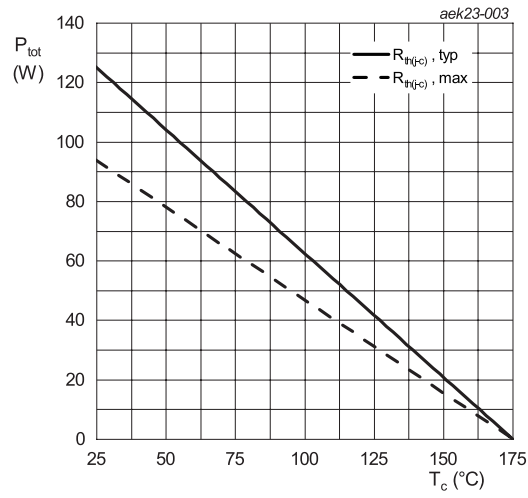
$$I_{F(AV)} = I_{F(RMS)} \times \sqrt{\delta}$$

$$V_o = 1.140\text{ V}; R_s = 0.1577\text{ }\Omega$$

**Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values**



**Fig. 2. Current derating as a function of case temperature**



**Fig. 3. Total power dissipation as a function of case temperature**

## 9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-c)}$	thermal resistance from junction to case	<a href="#">Fig. 4</a>	-	1.2	1.6	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient free air	in free air	-	50	-	K/W

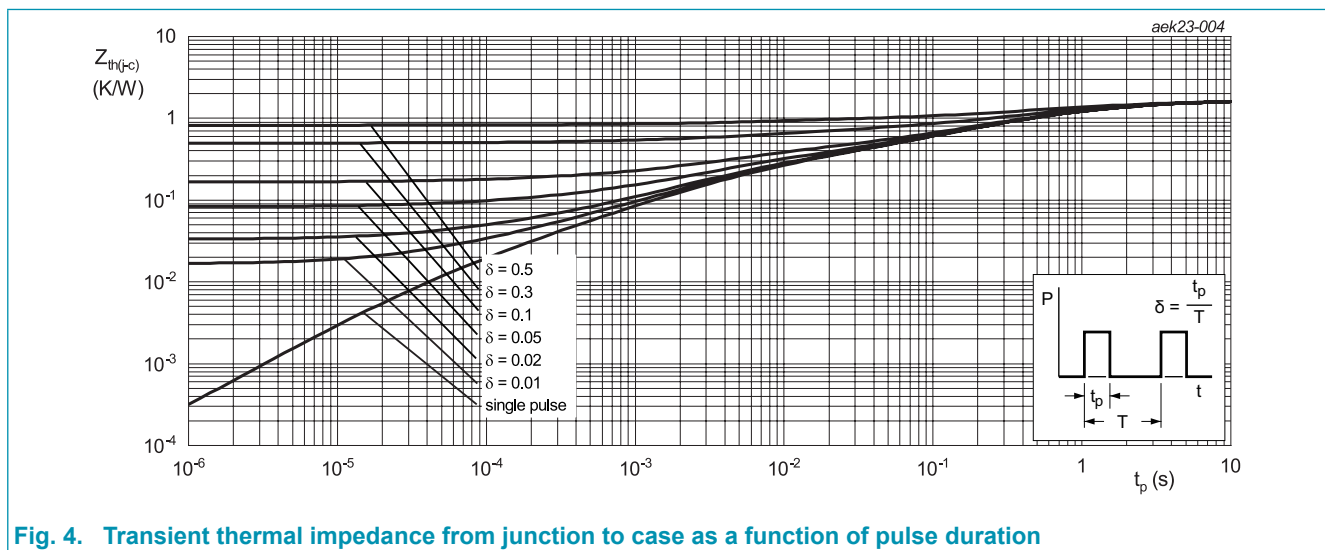
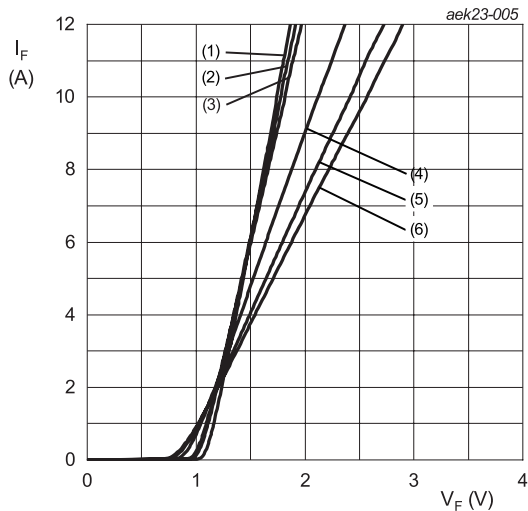


Fig. 4. Transient thermal impedance from junction to case as a function of pulse duration

## 10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
$I_F$	forward current	$I_F = 6 \text{ A}; T_j = 25 \text{ }^\circ\text{C}; \text{ Fig. 5}$	-	1.5	1.7	V
		$I_F = 6 \text{ A}; T_j = 150 \text{ }^\circ\text{C}; \text{ Fig. 5}$	-	1.8	2.1	V
		$I_F = 6 \text{ A}; T_j = 175 \text{ }^\circ\text{C}; \text{ Fig. 5}$	-	2	2.25	V
$I_R$	reverse current	$V_R = 650 \text{ V}; T_j = 25 \text{ }^\circ\text{C}; \text{ Fig. 6}$	-	-	40	$\mu\text{A}$
		$V_R = 650 \text{ V}; T_j = 175 \text{ }^\circ\text{C}; \text{ Fig. 6}$	-	-	160	$\mu\text{A}$
<b>Dynamic characteristics</b>						
$Q_r$	recovered charge	$I_F = 6 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A}/\mu\text{s}; T_j = 25 \text{ }^\circ\text{C}; \text{ Fig. 7}$	-	9	-	nC
$C_d$	diode capacitance	$f = 1 \text{ MHz}; V_R = 1 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	-	190	-	pF
		$f = 1 \text{ MHz}; V_R = 300 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	-	30	-	pF
		$f = 1 \text{ MHz}; V_R = 600 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	-	29	-	pF
$E_{as}$	non-repetitive avalanche energy	$I_R = 4.25 \text{ A}; L = 5 \text{ mH}; T_{j(\text{init})} = 25 \text{ }^\circ\text{C}$	45	-	-	mJ



$V_o = 1.140 \text{ V}; R_s = 0.1577 \text{ } \Omega$   
 (1)  $T_j = -55 \text{ }^\circ\text{C};$  typical values  
 (2)  $T_j = 0 \text{ }^\circ\text{C};$  typical values  
 (3)  $T_j = 25 \text{ }^\circ\text{C};$  typical values  
 (4)  $T_j = 100 \text{ }^\circ\text{C};$  typical values  
 (5)  $T_j = 150 \text{ }^\circ\text{C};$  typical values  
 (6)  $T_j = 175 \text{ }^\circ\text{C};$  typical values

Fig. 5. Forward current as a function of forward voltage; typical values

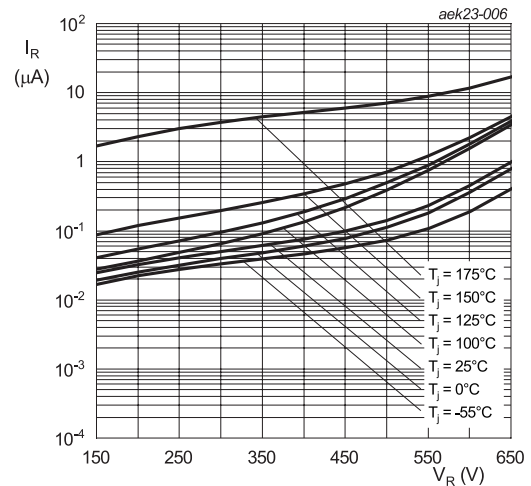
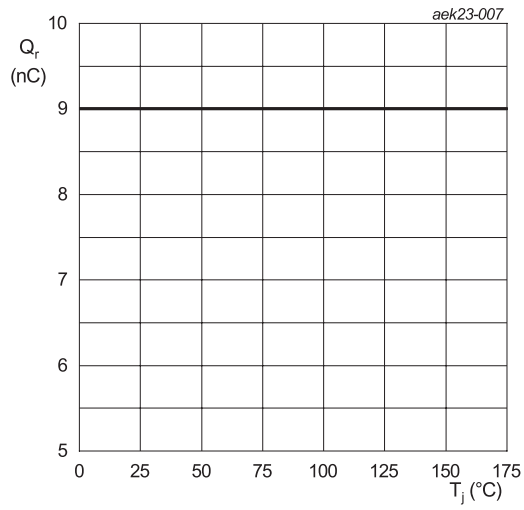
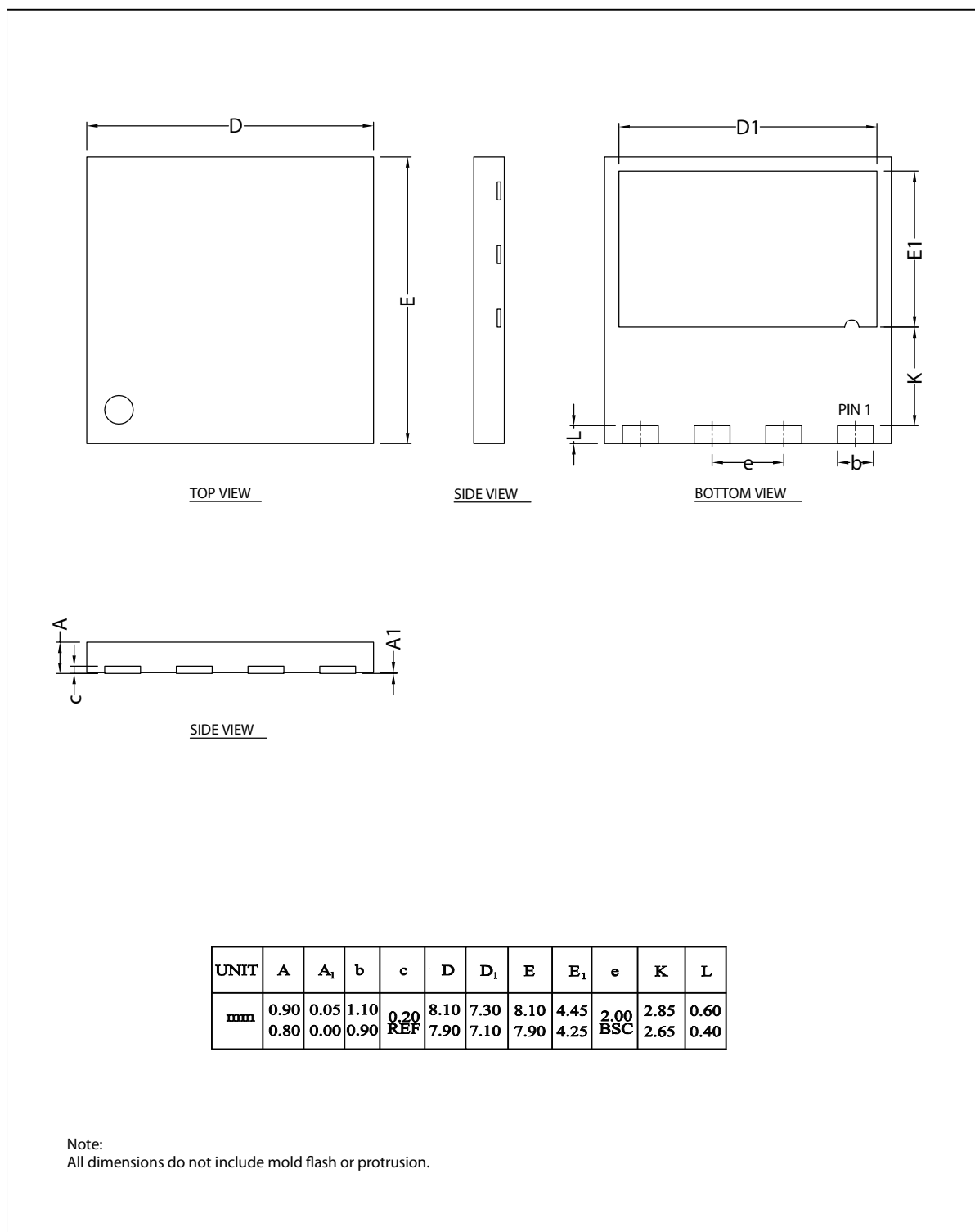


Fig. 6. Reverse leakage current as a function of reverse voltage; typical value



**Fig. 7. Recovered charge as a function of junction temperature**

## 11. Package outline



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